

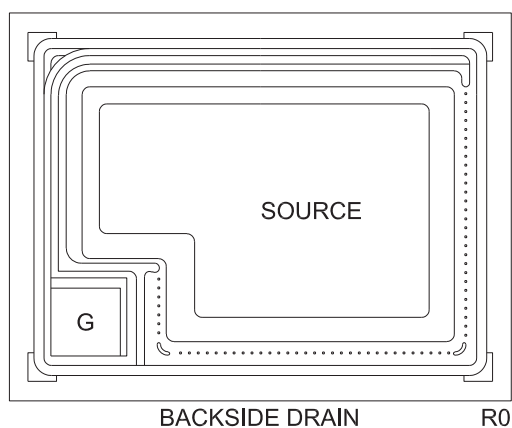
PROCESS CP757X
Small Signal MOSFET Transistor
P-Channel Enhancement-Mode MOSFET Chip



PROCESS DETAILS

Die Size	22 x 17 MILS
Die Thickness	5.9 MILS
Gate Bonding Pad Area	3.9 x 3.9 MILS
Source Bonding Pad Area	14 x 9 MILS
Top Side Metalization	Al-Si - 30,000Å
Back Side Metalization	Au - 12,000Å

GEOMETRY



GROSS DIE PER 6 INCH WAFER

63,570

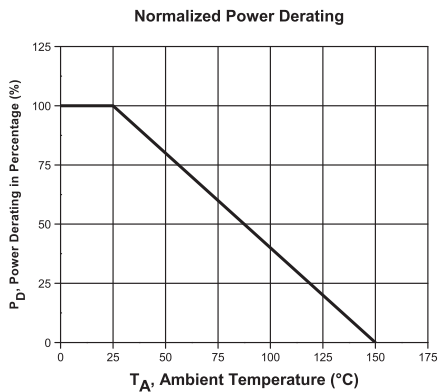
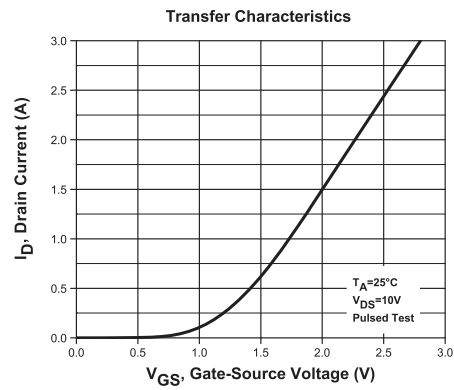
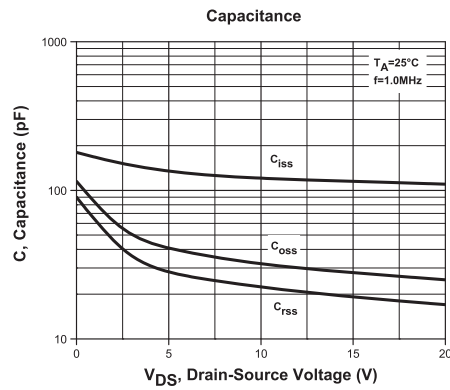
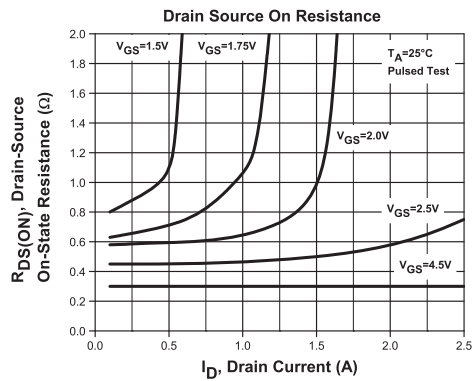
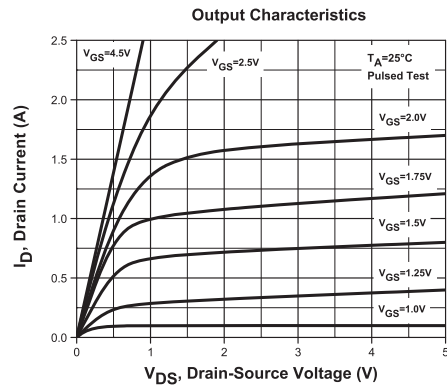
PRINCIPAL DEVICE TYPE

CMLDM5757

R0 (2-December 2010)

PROCESS CP757X

Typical Electrical Characteristics



R0 (2-December 2010)